



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

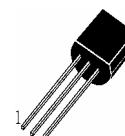
H327**SWITCHING AND AMPLIFIER APPLICATIONS**

Suitable for AF-Driver stages and low power output stages

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation.....	625mW
V_{CBO}	Collector-Base Voltage.....	-50V
V_{CEO}	Collector-Emitter Voltage.....	-45V
V_{EBO}	Emitter-Base Voltage.....	-5V
I_C	Collector Current.....	-500mA

TO-92



- 1 Collector , C
- 2 Base , B
- 3 Emitter , E

ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-50			V	$I_C=-100 \mu A, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	-45			V	$I_C=-10mA, I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	$I_E=-100 \mu A, I_C=0$
I_{CBO}	Collector Cut-off Current			-100	nA	$V_{CB}=-20V, I_E=0$
I_{EBO}	Emitter-Base Cut-off Current			-10	μA	$V_{EB}=-5V, I_C=0$
$H_{FE} (1)$	DC Current Gain	100		600		$V_{CE}=-1V, I_C=-100mA$
$H_{FE} (2)$	DC Current Gain	40				$V_{CE}=-1V, I_C=-500mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-0.7	V	$I_C=-500mA, I_B=-50mA$
$V_{BE(ON)}$	Base-Emitter On Voltage			-1.2	V	$V_{CE}=-1V, I_C=-500mA$
f_T	Current Gain-Bandwidth Product		100		MHz	$V_{CE}=-5V, I_C=-10mA$
C_{cbo}	Collector-Base Capacitance		8		pF	$V_{CB}=-10V, I_E=0$ $F=1MHz$

 h_{FE} Classification

16

25

40

100—250

160—400

250—600

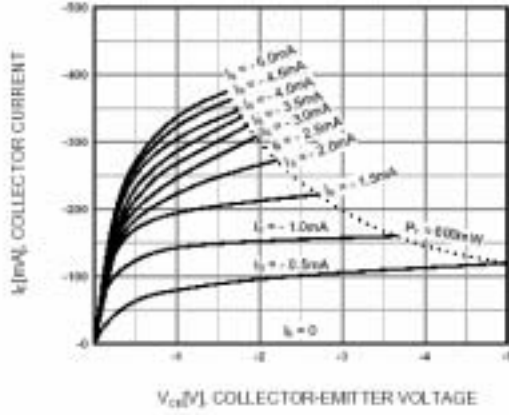


Figure 1. Static Characteristic

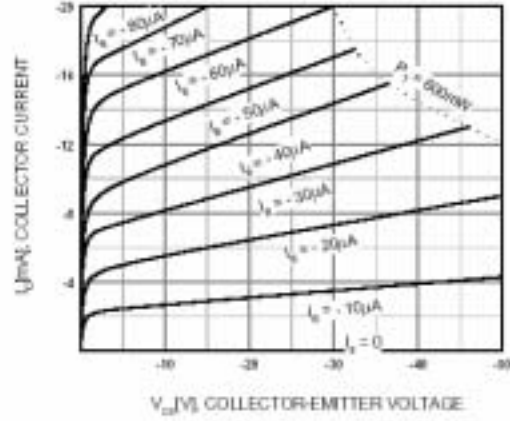


Figure 2. Static Characteristic

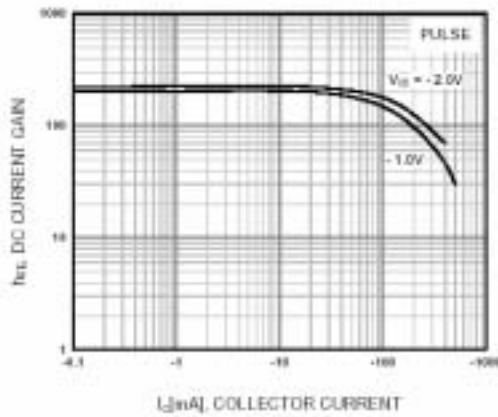


Figure 3. DC current Gain

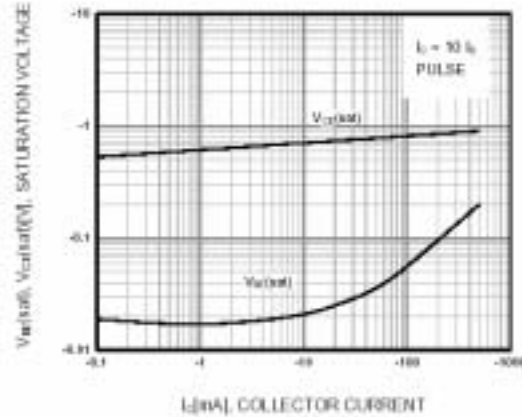


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

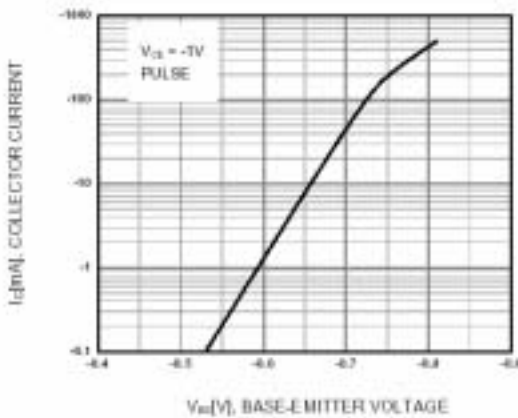


Figure 5. Base-Emitter On Voltage

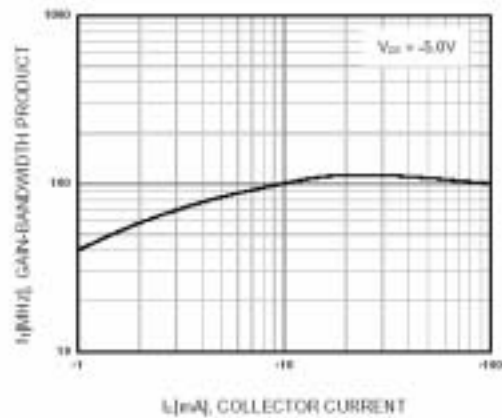


Figure 6. Gain Bandwidth Product